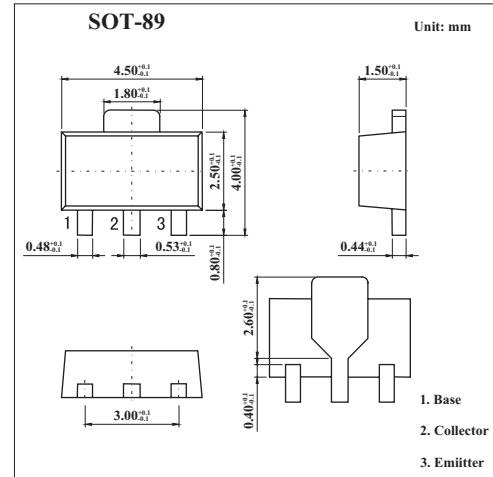


Surface Mount PNP Silicon Transistor

KXT5401 (CXT5401)

■ Features

- High current (max. 500mA).
- Low voltage (max. 150 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-160	V
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current (DC)	I _c	-500	mA
power dissipation	P _D	1.2	W
thermal resistance Junction- to-ambient	R _{θJA}	104	°C/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{CB0}	I _C = -100 μA	-160			V
Collector to emitter breakdown voltage	V _{CEO}	I _C = -1.0mA	-150			V
Emitter to base breakdown voltage	V _{EBO}	I _E = -10 μA	-5.0			V
Collector cutoff current	I _{CBO}	V _{CB} = -120 V, I _E = 0			-50	nA
		V _{CB} = -120 V, T _A = 100°C			-50	μA
DC current gain	h _{FE}	I _C = -1.0 mA; V _{CE} = -5.0 V	50			
		I _C = -10 mA; V _{CE} = -5.0V	60		240	
		I _C = -50 mA; V _{CE} = -5.0V	50			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA; I _B = -1.0mA			-0.2	V
		I _C = -50 mA; I _B = -5.0mA			-0.5	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = -10 mA; I _B = -1.0mA			-1.0	V
		I _C = -50 mA; I _B = -5.0mA			-1.0	V
Output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1.0MHz			6.0	pF
Transition frequency	f _T	I _C = -10 mA; V _{CE} = -10V; f = 100 MHz	100		300	MHz